

innodisk

市场信息及产品更新

2025 7月 宜鼎国际

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DRAM 市场 & 产品最新信息

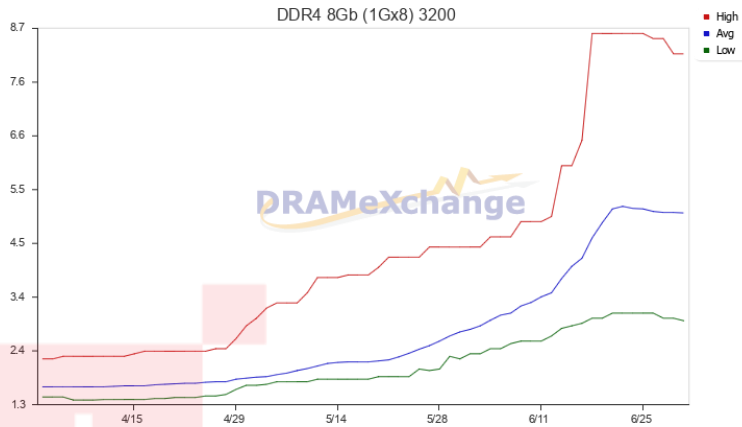
Innodisk DRAM Business Unit

内存市场状况

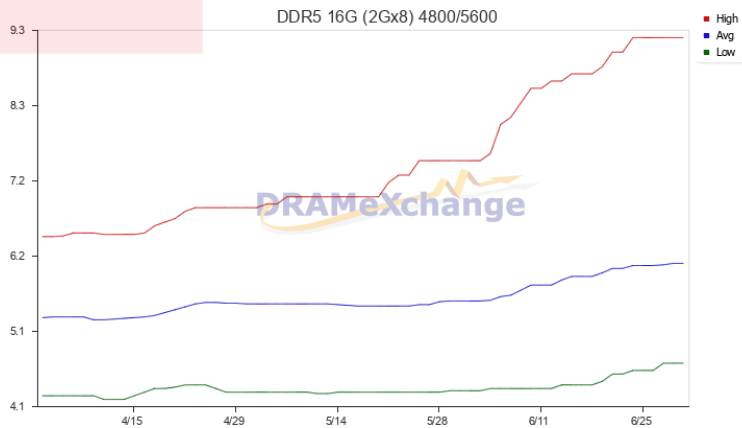
■ DRAM价格飙升，舊世代产品价格大幅上涨：由于DRAM IC供货商纷纷转向HBM等高端产品，并宣布DDR4和LPDDR4X等老一代规格产品停产，市场出现了恐慌性抢购。预计2025年第三季DRAM价格将全线上涨，其中消费性与PC应用的DDR4 DRAM价格较上季上涨40-45%，涨幅远超DDR5等新产品。

■ 为应对DDR4缺货，宜鼎国际已准备了全系列的替代规格，并推出了DDR4南亚解决方案。我们也预计推出使用南亚IC的内存模块，产品寿命将维持到2030年。如需了解替代规格的详细规格，请联络您的宜鼎国际销售。

DDR4 8Gb IC现货价格趋势



DDR5 16Gb IC现货价格趋势



DRAM IC Longevity

2025 Q2

2025 Q3

2025 Q4

2026 Q1

2026 Q2

2026 Q3

DDR5



5600/6400 1αnm
16Gb A-die

5600/6400 1bnm
24Gb/32Gb M-die

SAMSUNG

5600 1αnm 16Gb P-die

1αnm shared production capacity with HBM3E, so the supply might be affected in Q4 2025.

DDR4

micron

3200 1αnm(Shortage & Limited supply)
8/16Gb R/F-die by Embedded team

We expect Micron to have longevity support till 2030 Jan.



3200 1znm(Shortage, will be EOL later)
8/16Gb E/D-die by Consumer/IPC team

SAMSUNG

3200 1znm(Shortage & Limited supply)
4/8/16Gb G/G/C-die by Consumer/IPC

Samsung is having limited supply for 1znm since 2025 Q2.



3200 1B(16 nm) Longevity supply
4/8Gb F/H-die

Nanya can support small capacity of DDR4 with better longevity till 2030.

DDR3

micron

1866 1ynm 4Gb P-die

We expect Micron to have longevity support till 2030 Jan.



1866 20nm 4Gb R-die

We expect Winbond to have longevity support till 2028 Q1.

内存新产品

Innodisk Unveils DDR5 6400 64GB DRAM Series to Empower Edge AI and Generative AI Applications



Innodisk announces its DDR5 6400 DRAM series, featuring the industry's largest 64GB single-module capacity. This 6400 series is purpose-built for data-intensive applications in AI, telehealth, and edge computing, where high performance at the edge is crucial. Available in versatile form factors, including [CUDIMM](#), [CSODIMM](#), and RDIMM, the series delivers unmatched speed, stability, and capacity to meet the rigorous demands of modern edge AI and industrial applications.

NAND闪存市场信息



NAND Flash Industry Review

NAND原厂MLC、256Gb颗粒停产不回头 重演DDR4涨价大戏

NAND闪存市场近期出现剧烈变化，多家原厂“下定决心”停产MLC NAND与256Gb TLC NAND，导致中低容量芯片供应紧张，价格快速上涨，市场再现类似DDR4内存停产后价格暴涨的局面。

产业链消息显示，MLC NAND停产使得工业控制、车载电子等特殊应用面临原材料断供风险，现有库存成为抢手货。64Gb MLC NAND现货价格已突破5美元，较最低谷时的0.8美元涨幅超六倍。256Gb TLC NAND价格也从年初的每颗1.6美元上涨至二季度末的2.5美元，主流512Gb以下产品全线缺货。

各大原厂将产能转向先进工艺与大容量产品，如1Tb芯片、QLC NAND及堆叠技术（如BiCS8、V9），这表明NAND闪存市场正在加速升级转型。部分厂商同时采取自产自用策略，进一步减少了对外供货量。

虽然消费电子产品多已转向大容量NAND，但市场仍存在大量无法升级换代的应用场景，如智能电视、物联网设备、车载系统等小容量需求。这些细分市场的旺盛需求支撑着中低容量NAND价格维持高位，并带来更高利润空间。

在大容量与细分市场双重驱动下，NAND闪存市场供需格局正在重构，价格获得支撑、厂商盈利能力同步提升，为产业发展注入了新的增长动力。



NAND Flash Industry Outlook

AI推动闪存控制器爆发式增长，第六代传输速度翻倍成关键

随着人工智能技术快速发展，闪存芯片的战略地位不断提升，带动闪存控制器市场规模持续扩大。作为直接影响AI运算性能的关键部件，高性能闪存控制器备受业界关注，其中传输速率实现跨越式提升的第六代产品更被视为决定未来市场格局的核心要素。

据韩国媒体ZDNet Korea援引调研机构Global Information的预测数据，全球固态硬盘市场规模预计将从2024年的654.7亿美元增长至2029年的1470.1亿美元，年均复合增长率高达17.56%。作为固态硬盘的核心控制单元，闪存控制器承担着数据存储与传输的关键职能，其市场需求随之水涨船高。

市场格局正在发生深刻变革：传统以消费电子为主导的闪存市场，正随着AI数据中心建设热潮而向企业级应用倾斜。以美国芯片设计巨头Marvell为例，该公司已战略性收缩消费级产品线，重点布局企业级市场，并推出第五代PCIe控制器新品，积极抢占云计算服务商等高端客户资源。

这种战略转型的背后是显著的利润差异：企业级控制器凭借定制化设计需求和高技术门槛，利润率普遍超过30%；而深陷价格战的消费级产品利润率仅维持在10%左右。业内人士分析指出，这种结构性差异将持续推动产业链向高附加值领域转型。

Flash产品更新



Innodisk Datacenter SSD

Reliability

Datacenters are running 24/7. High-reliability SSDs are essential to support the workload and data integrity.

Endurance

SSDs for datacenter should possess good endurance level for constant write and erase operations.

Performance

Datacenters process massive amount of data. High-performance and low latency is needed for the high data demand.

Security

SSDs with security features help to protect data against any unauthorized access or attack

Maintenance

Minimizing service down-time is critical. Reducing any debugging effort helps to improve datacenter operating efficiency.

Customization

Innodisk is able to customize the solution to meet the specific requirements of an application.

**Meeting the Key Aspects in
Modern Datacenters**

Product Highlight

Datcenter Boot SSD Selection



SATA 3TS9-P Series

Form Factors	2.5" SSD, M.2 2280		
Seq. Read/Write	550/520 MB/s (max.)		
Endurance (JEDEC 219, Enterprise workload, Warranty 5 Years)	Application	Recommended Capacity*	DWPD
	Mainstream	240GB-960GB	1
Operation Temp.	0°C - 70°C		



PCIe 4TS2-P Series

Form Factors	U.2, M.2 2280, M.2 22110, E1.S		
Seq. Read/Write	6950/4100 MB/s (max.)		
Endurance (JEDEC 219, Enterprise workload, Warranty 5 Years)	Application	Recommended Capacity*	DWPD
	Mainstream	240GB-960GB	1
Operation Temp.	0°C - 70°C		

*Higher capacity available. Please refer to product datasheet for more info.

Product Highlight

Data Center Storage SSD- PCIe Gen5



Features

- 3D eTLC/QLC
- NVMe 2.0
- Innodisk DSSD Feature Set
- Enhanced Thermal Management
- Customizable Features
- OCP 2.0

PCIe 5TS-P / 5QS-P Series

Form Factors	U.2, E1.S, E3.S, E3.L		
Seq. Read/Write	14 / 10 GB/s (max.)		
Endurance (JEDEC 219, Enterprise workload, Warranty 5 Years)	Application	Capacity*	DWPD
	Mainstream (eTLC)	1.9TB-15.3TB	1
	Mixed-use (eTLC)	1.6TB-12.8TB	3
	High-capacity (E3.L QLC)	128TB	TBA



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